

Silicon PNP Power Transistors

2SB449

DESCRIPTION

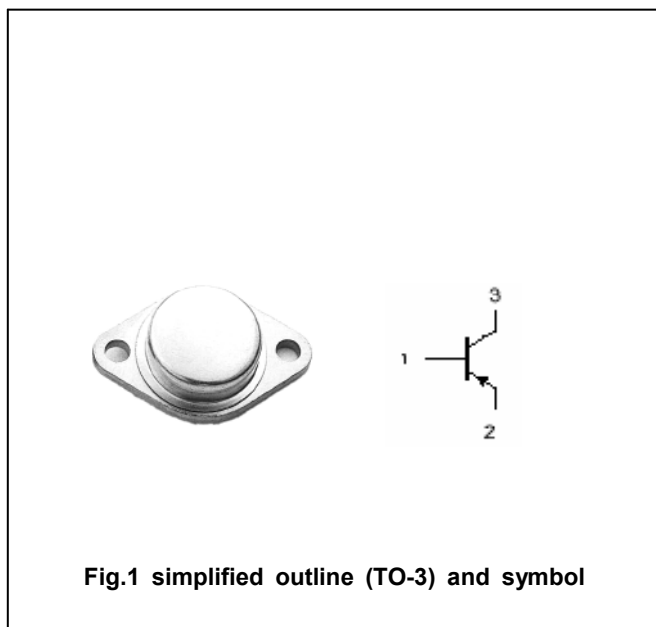
- With TO-3 package
- Low collector saturation voltage
- Wide area of safe operation

APPLICATIONS

- Power amplifier applications
- Power switching applications
- DC-DC converters

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-50	V
V_{CEO}	Collector-emitter voltage	Open base	-50	V
V_{EBO}	Emitter-base voltage	Open collector	-7	V
I_C	Collector current		-3.5	A
P_C	Collector power dissipation	$T_C = 50 \square$	22.5	W
T_j	Junction temperature		150	\square
T_{stg}	Storage temperature		-55~150	\square

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CHARACTERISTICS

T_j=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =-10mA ; I _B =0	-50			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =-1mA ; I _E =0	-50			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA ; I _C =0	-7			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-3A; I _B =-0.3A			-0.7	V
V _{BEsat}	Base-emitter saturation voltage	I _C =-3A; I _B =-0.3A			-1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =-50V; I _E =0			-10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =-7V; I _C =0			-10	μA
h _{FE}	DC current gain	I _C =-3A ; V _{CE} =-2V	20		85	

PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.1mm)